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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Hisashi OHTANI et al.

Serial No. 08/807,737

Filed: February 27, 1997

For: METHOD FOR MANUFACTURING
SEMICONDUCTOR DEVICE

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Examiner: Evan PERT

Group Art Unit: 2829

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INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
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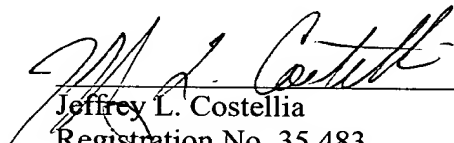
Sir:

In accordance with the duty of disclosure as set forth in 37 C.F.R. §1.56, Applicants hereby submit the following information in conformance with 37 C.F.R. §§ 1.97 and 1.98. Pursuant to 37 C.F.R. § 1.98, a copy of each of the documents cited is enclosed.

It is requested that the accompanying PTO-1449 be considered and made of record in the above-identified application. To assist the Examiner, the documents are listed on the attached form PTO-1449. It is respectfully requested that an Examiner initial a copy of this form be returned to the undersigned.

The Commissioner is hereby authorized to charge any fees connected with this filing which may be required now, or credit any overpayment to Deposit Account No. 19-2380 (740756-1638).

Respectfully submitted,



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Form PTO-1449 (Rev. 8-83)		U.S. Department of Commerce Patent and Trademark Office		Attorney Docket No. 0756-1638		Serial No. 08/807,737	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)							
				Applicant: Hisashi OHTANI et al.			
				Filing Date: February 27, 1997		Group: 2829	
U.S. PATENT DOCUMENTS							
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)	
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OFFICE OF PETITIONS				FOREIGN PATENT DOCUMENTS			
	Document Number	Date	Country	Class	Subclass	Translation Yes No	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
	✓	Tamura et al, "Oriented Crystal Growth of Si on SiO ₂ Patterns by Pulse Ruby Laser Annealing" Proceedings of the 12 th Conference on Solid State Devices, Tokyo (1980), pp. 43-48					
	✓	H. R. Wenk et al. "Texture Analysis of Polycrystalline Silicon Films" J. Appl. Phys. 67 (1) 1/1/1990 pp. 572-574					
	✓	T.I. Kamins "Design Properties of Polycrystalline Silicon" Sensors and Actuators, A21-A23 (1990) pp. 817-828					
	✓	Yunosuke KAWAZU et al. "Low-Temperature Crystallization of Hydrogenated Amorphous Silicon Induced by Nickel Silicide Formation" Institute of Applied Physics, University of Tsukuba, pp.2698-2704 (10/20/1990)					
	✓	Nagarajan Sridhar et al. "Polysilicon films of high photoresponse, obtained by vacuum annealing of aluminum capped hydrogenated amorphous silicon" J. Appl. Phys. 78 (12) pp. 7304-7312 (12/15/1995)					
	✓	T. Noma et al. "Crystal forms by solid-state recrystallization of amorphous Si films" Appl. Phys. Lett. 59 (6) pp. 653-655 (08/05/1991)					
	✓	Hiroyuki KURIYAMA et al. "Comprehensive Study of Lateral Grain Growth in Poly-Si Films by Excimer Laser Annealing and Its Application to Thin Film Transistors" Jpn. J. Appl. Phys., Vol. 33 (1994) pp. 5567-5662 (10/10/1994)					
Examiner			Date Considered				
*EXAMINER : Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							